FEATURES

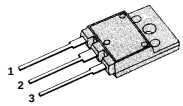
- Avalanche Rugged Technology
- Rugged Gate Oxide Technology
- Lower Input Capacitance
- Improved Gate Charge
- Extended Safe Operating Area
- Lower Leakage Current: 25μA (Max.) @ V_{DS} = 900V
- Lower $R_{DS(ON)}$: 0.938Ω (Typ.)

BV_{DSS} = 900V

$R_{DS(ON)}$ = 1.2Ω

I_D = 10A

TO-3P



1. Gate 2. Drain 3. Source

ABSOLUTE MAXIMUM RATINGS

Symbol	Characteristics	Value	Units
V_{DSS}	Drain-to-Source Voltage	900	V
I_D	Continuous Drain Current (T_C = 25°C)	10	A
	Continuous Drain Current (T_C = 100°C)	6.3	
I_{DM}	Drain Current-Pulsed ①	40	A
V_{GS}	Gate-to-Source Voltage	±30	V
E_{AS}	Single Pulsed Avalanche Energy ②	794	mJ
I_{AR}	Avalanche Current ①	10	A
E_{AR}	Repetitive Avalanche Energy ①	28	mJ
dv/dt	Peak Diode Recovery dv/dt ③	1.5	V/ns
P_D	Total Power Dissipation (T_C = 25°C) Linear Derating Factor	280 2.22	W W/°C
T_J, T_{STG}	Operating Junction and Storage Temperature Range	–55 to +150	°C
T_L	Maximum Lead Temp. for Soldering Purposes, 1/8” from case for 5-seconds	300	

THERMAL RESISTANCE

Symbol	Characteristics	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	–	0.45	°C/W
$R_{\theta CS}$	Case-to-Sink	0.24	–	
$R_{\theta JA}$	Junction-to-Ambient	–	40	

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise specified)

Symbol	Characteristics	Min.	Typ.	Max.	Units	Test Conditions
BV_{DSS}	Drain-Source Breakdown Voltage	900	–	–	V	V_{GS}=0V, I_D=250μA
$\Delta BV/\Delta T_J$	Breakdown Voltage Temp. Coeff.	–	1.11	–	V/°C	I_D=250μA, ***See Fig 7***
$V_{GS(th)}$	Gate Threshold Voltage	2.0	–	3.5	V	V_{DS}=5V, I_D=250μA
I_{GSS}	Gate-Source Leakage, Forward	–	–	100	nA	V_{GS}=30V
	Gate-Source Leakage, Reverse	–	–	–100		V_{GS}= –30V
I_{DSS}	Drain-to-Source Leakage Current	–	–	25	μA	V_{DS}=900V
		–	–	250		V_{DS}=720V, T_C=125°C
$R_{DS(on)}$	Static Drain-Source On-State Resistance	–	–	1.2	Ω	V_{GS}=10V, I_D=5A ④
g_{fs}	Forward Transconductance	–	7.85	–	S	V_{DS}=50V, I_D=5A ④
C_{iss}	Input Capacitance	–	2760	3580	pF	V_{GS}=0V, V_{DS}=25V f=1MHz ***See Fig 5***
C_{oss}	Output Capacitance	–	245	290		
C_{rss}	Reverse Transfer Capacitance	–	105	125		
$t_{d(on)}$	Turn-On Delay Time	–	29	70	ns	V_{DD}=450V, I_D=10A R_G=9.6Ω ***See Fig 13*** ④ ⑤
t_r	Rise Time	–	54	20		
$t_{d(off)}$	Turn-Off Delay Time	–	161	330		
t_f	Fall Time	–	47	105		
Q_g	Total Gate Charge	–	127	165	nC	V_{DS}=720V, V_{GS}=10V I_D=10A ***See Fig 6 & Fig 12*** ④ ⑤
Q_{gs}	Gate-Source Charge	–	19.2	–		
Q_{gd}	Gate-Drain (Miller) Charge	–	56.8	–		

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS

Symbol	Characteristics	Min.	Typ.	Max.	Units	Test Conditions
I_S	Continuous Source Current	–	–	10	A	Integral reverse pn-diode in the MOSFET
I_{SM}	Pulsed-Source Current ①	–	–	40		
V_{SD}	Diode Forward Voltage ④	–	–	1.4	V	T_J=25°C, I_S=10A, V_{GS}=0V
t_{rr}	Reverse Recovery Time	–	690	–	ns	T_J=25°C, I_F=10A di_F/dt=100A/μs ④
Q_{rr}	Reverse Recovery Charge	–	11.94	–	μC	

Notes:

① Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
② L=15mH, I_{AS}=10A, V_{DD}=50V, R_G=27Ω, Starting T_J =25°C
③ $I_{SD} \leq$ 10A, di/dt ≤ 190A/μs, $V_{DD} \leq BV_{DSS}$, Starting T_J =25°C
④ Pulse Test: Pulse Width ≤ 250μs, Duty Cycle ≤ 2%
⑤ Essentially Independent of Operating Temperature

Fig 1. Output Characteristics

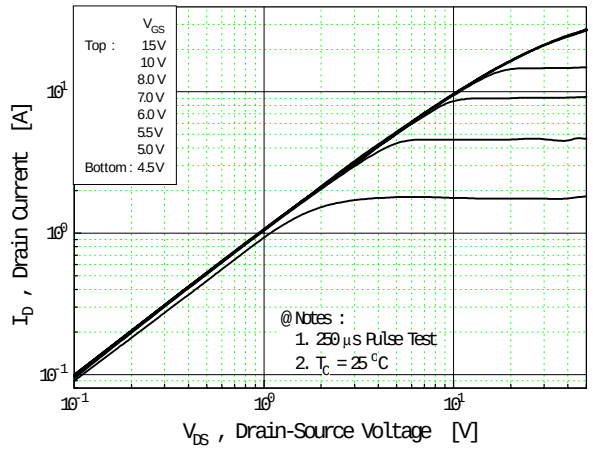


Fig 2. Transfer Characteristics

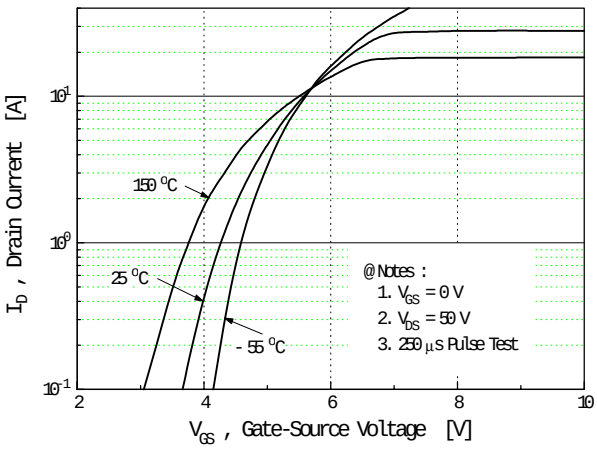


Fig 3. On-Resistance vs. Drain Current

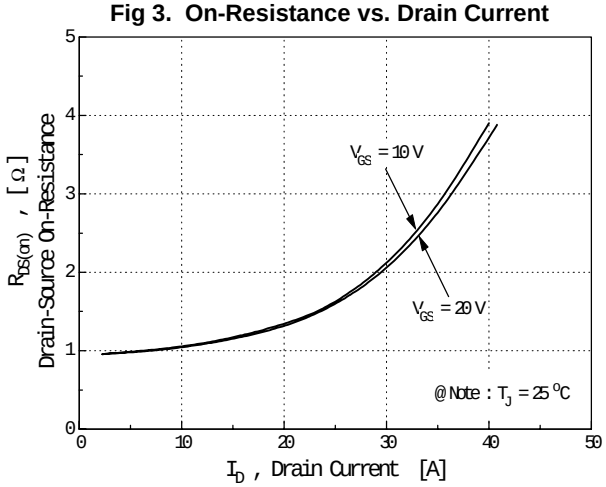


Fig 4. Source-Drain Diode Forward Voltage

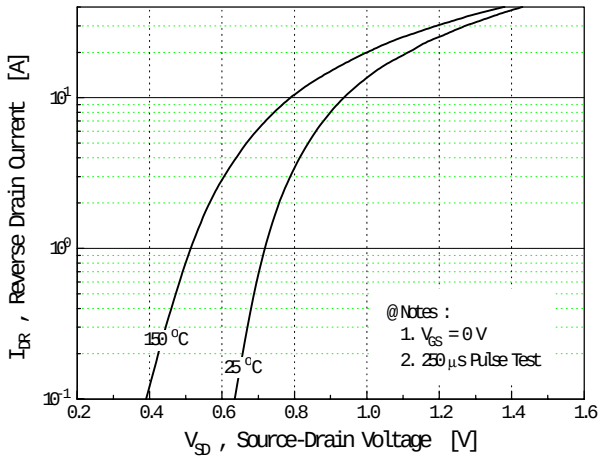


Fig 5. Capacitance vs. Drain-Source Voltage

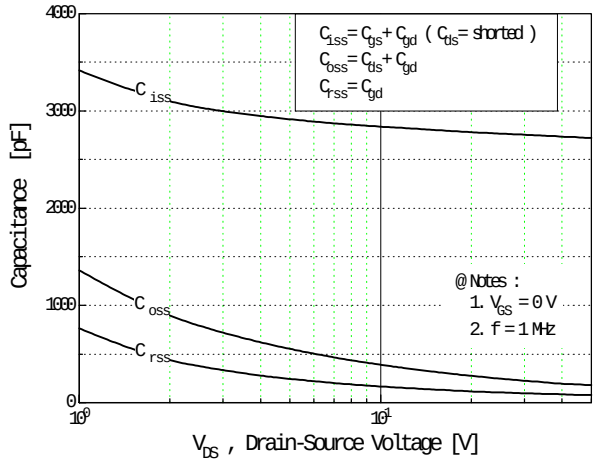


Fig 6. Gate Charge vs. Gate-Source Voltage